# Notification about the transfer of the semiconductor business

The semiconductor business of Panasonic Corporation was transferred on September 1, 2020 to Nuvoton Technology Corporation (hereinafter referred to as "Nuvoton"). Accordingly, Panasonic Semiconductor Solutions Co., Ltd. became under the umbrella of the Nuvoton Group, with the new name of Nuvoton Technology Corporation Japan (hereinafter referred to as "NTCJ").

In accordance with this transfer, semiconductor products will be handled as NTCJ-made products after September 1, 2020. However, such products will be continuously sold through Panasonic Corporation.

Publisher of this Document is NTCJ.

If you would find description "Panasonic" or "Panasonic semiconductor solutions", please replace it with NTCJ.

\* Except below description page

"Request for your special attention and precautions in using the technical information and semiconductors described in this book"

Nuvoton Technology Corporation Japan



# MOS FET SK8403200L

Unit: mm

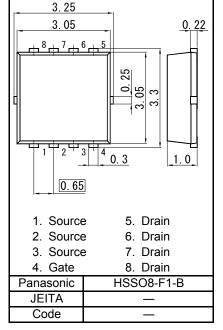
# SK8403200L Silicon N-channel MOSFET

For Li-ion battery / for DC-DC converter

#### Features

- Low drain-source ON resistance:RDS(on)typ. = 3.7 mΩ (VGS = 10 V)
- Halogen-free / RoHS compliant
- (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)
- Marking Symbol: 1A
- Packaging

Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

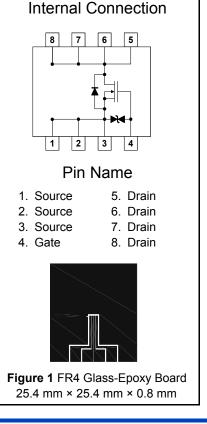


### ■ Absolute Maximum Ratings Ta = 25 °C

Parameter		Symbol	Rating	Unit	
Drain-source Voltage		VDSS	30	V	
Gate-source Voltage		VGSS	±20	V	
Drain current	Drain current		23	А	
Drain current(Pulsed) t=1ms		IDp <sup>*1 *2</sup>	81.5	А	
Total Power	Ta = 25 °C, t = 10 s	PD <sup>*1 *2</sup>	2	W	
Dissipation	Tc = 25 °C	PD <sup>*1 *2</sup>	30	vv	
Thermal	Channel to Ambient	Rth(ch-a)	62.5	°C/W	
Resistance	Channel to Case	Rth(ch-c)	4.1	-07.00	
Channel Temp	perature	Tch	150	°C	
Storage Temperature Range		Tstg	-55 to +150	°C	

Note \*1 Device mounted on a glass-epoxy board in Figure 1

\*2 Pulse test: Ensure that the channel temperature does not exceed 150 °C





MOS FET SK8403200L

### ■ Electrical Characteristics Ta = 25 °C ± 3 °C

### Static Characteristics

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	VDSS	ID = 1.0 mA, VGS = 0 V	30			V
Zero Gate Voltage Drain Current	IDSS	VDS = 30 V, VGS = 0 V			10	μA
Gate-source Leakage Current	IGSS	VGS = ±16 V, VDS = 0 V			±10	μA
Gate-source Threshold Voltage	Vth	ID = 2.3 mA, VDS = 10 V	1.0		2.5	V
Drain-source On-State Resistance	RDS(on)1	ID = 11.5A, VGS = 10 V		3.7	5.0	mΩ
	RDS(on)2	ID = 11.5A, VGS = 4.5V		5.4	8.1	

#### **Dynamic Characteristics**

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Input Capacitance	Ciss	VDS = 10 V, VGS = 0 V f = 1 MHz		1800		pF
Output Capacitance	Coss			230		
Reverse Transfer Capacitance	Crss			150		
Turn-on Delay Time <sup>*1</sup>	td(on)	VDD = 15 V, VGS = 0 to 10 V		11		
Rise Time <sup>*1</sup>	tr	ID = 11.5 A		6		ns
Turn-off Delay Time <sup>*1</sup>	td(off)	VDD = 15 V, VGS = 10 to 0 V		62		20
Fall Time <sup>*1</sup>	tf	ID = 11.5 A		9		ns
Total Gate Charge	Qg			14		nC
Gate-source Charge	Qgs	VDD = 15 V, VGS = 0 to 4.5 V, ID = 23 A		4.5		
Gate-drain Charge	Qgd	ID = 23 A		5		

Note \*1 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

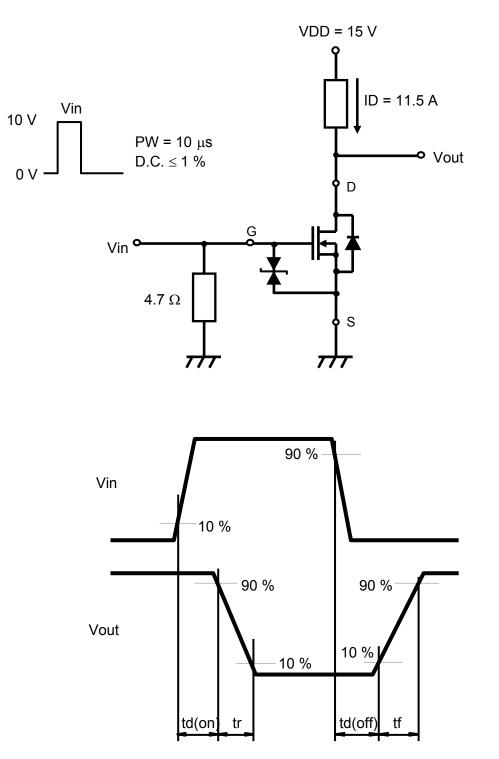
## Body Diode Characteristic

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Diode Forward Voltage	VSD	IS = 11.5 A, VGS = 0 V		0.8	1.2	V

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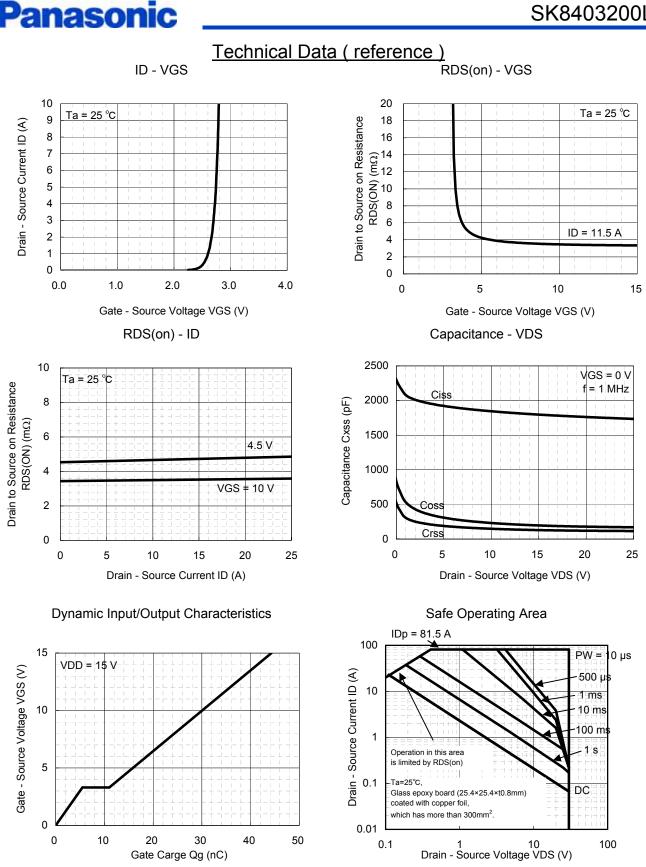


\*1 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

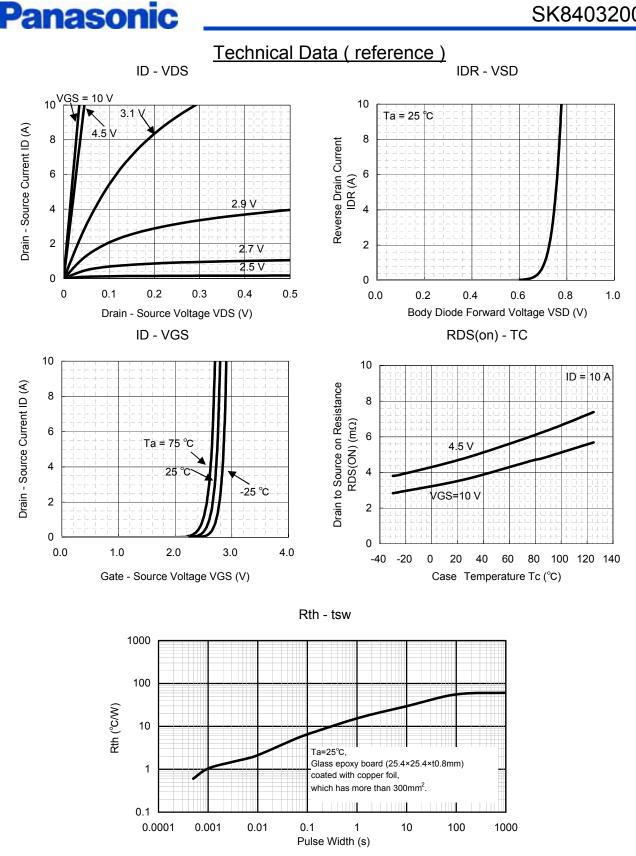




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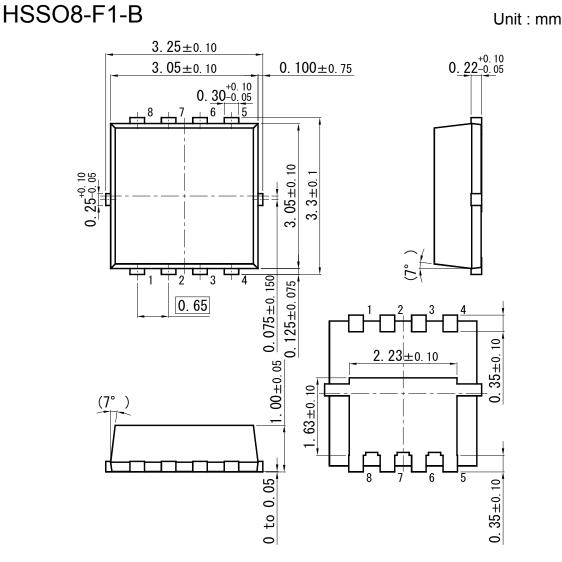


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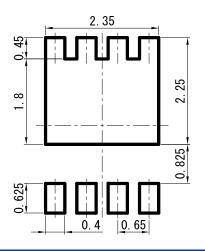




MOS FET SK8403200L



Land Pattern (Reference) (Unit: mm)



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